

Silicon Rf Power Mos Fet Discrete Rd70huf2

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Silicon Rf Power Mos Fet

< Silicon RF Power MOS FET (Discrete) > RD15HVF1

< Silicon RF Power MOS FET (Discrete) > RD15HVF1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 15W DESCRIPTION RD15HVF1 is a MOS FET type transistor specifically designed for VHF/UHF High power amplifiers applica -tions FEATURES High power and High Gain: Pout>15 W, Gp>14 dB @Vds=125 V,f=175 MHz High Efficiency: 60 1% (typ) on

< Silicon RF Power MOS FET (Discrete) > RD16HHF1

< Silicon RF Power MOS FET (Discrete) > RD16HHF1 RoHS Compliance, Silicon MOSFET Power Transistor 30MHz,16W DESCRIPTION RD16HHF1 is a MOS FET type transistor specifically designed for HF RF power amplifiers applications FEATURES High power gain: Pout>16W, Gp>16dB @Vdd=125V,f=30MHz APPLICATION For output stage of high power amplifiers in

< Silicon RF Power MOS FET (Discrete) > RD60HUF1

< Silicon RF Power MOS FET (Discrete) > RD60HUF1 RoHS Compliance, Silicon MOSFET Power Transistor 520MHz,60W DESCRIPTION RD60HUF1 is a MOS FET type transistor specifically designed for UHF High power amplifiers applications FEATURES High power and High Gain: Pout>60W, Gp>77dB @Vdd=125V,f=520MHz

< Silicon RF Power MOS FET (Discrete) > RD70HUF2

< Silicon RF Power MOS FET (Discrete) > RD70HUF2 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 530MHz, 70W DESCRIPTION

RD70HUF2 is MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications FEATURES 1 Supply with Tape and Reel 500 Units per Reel 2 Employing Mold Package 3 High Power and High

< Silicon RF Power MOS FET (Discrete) > RD07MVS1

< Silicon RF Power MOS FET (Discrete) > RD07MVS1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W, 72V

DESCRIPTION RD07MVS1 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications FEATURES High power gain:

< Silicon RF Power MOS FET (Discrete) > RD20HMF1

< Silicon RF Power MOS FET (Discrete) > RD20HMF1 RoHS Compliance, Silicon MOSFET Power Transistor, 900MHz, 20W

PublicationDate: Oct 2011 8 ATTENTION: 1 High Temperature ; This product might have a heat generation while operation, Please take notice that have

SILICON RF POWER MOSFETS - World Scientific

x SILICON RF POWER MOSFETS the packaging and RF testing team from Silicon Semiconductor Corporation for their roles in developing SL-MOSFET products for cellular base-station applications This book was prepared, after my return to academi 2003a i a, ns a part of my scholarly activities at North Carolina State University Once

< Silicon RF Power MOS FET (Discrete) > RD07MVS1

< Silicon RF Power MOS FET (Discrete) > RD07MVS1 RoHS Compliant, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

PublicationDate: Sep 2014 2 ELECTRICAL CHARACTERISTICS (Tc=25°C, UNLESS OTHERWISE NOTED) SYMBOL PARAMETER CONDITIONS

SILICON RF POWER MOSFETS - GBV

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< Silicon RF Power MOS FET (Discrete) > RD07MVS1

For output stage of high power amplifiers in < Silicon RF Power MOS FET (Discrete) > RD07MVS1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W, 72V DESCRIPTION RD07MVS1 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications FEATURES High power gain: Pout>7W, Gp>10dB@Vdd=72V, f=520MHz

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< Silicon RF Power MOS FET (Discrete) > RD70HUP2

< Silicon RF Power MOS FET (Discrete) > RD70HUP2 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 530MHz, 70W, 125V

DESCRIPTION RD70HUP2 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications FEATURES 1 Supply with Tape and Reel 500 Units per Reel 2 Employing Mold Package 3

RF MOSFET Power Devices Application Note Cost-Effective ...

Cost-Effective Low-Power Gain Matching of RF MOSFET Power Devices RF MOSFET Power Devices Application Note Revision A 7 2 Cost-Effective Low-Power Gain Matching of RF MOSFET Power Devices This application note will discuss the purpose and traditional techniques of using RF power to combine power semiconductors in RF power amplifiers

< Silicon RF Power MOS FET (Discrete) > RD07MVS2

< Silicon RF Power MOS FET (Discrete) > RD07MVS2 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W DESCRIPTION RD07MVS2 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications This device has an internal monolithic zener diode from gate to source for ESD protection FEATURES High power gain:

High-Voltage Silicon MOSFETs, GaN, and SiC: All have a place

High-Voltage Silicon MOSFETs, GaN, and SiC: All have a place Philip Zuk, Director of Market Development, High-Voltage MOSFET Group, Vishay Siliconix - June 20, 2012 Questions have arisen about how silicon will compete against wide bandgap (WBG) materials such as Silicon Carbide (SiC) and Gallium Nitride (GaN)

A Manufacturing Cost and Supply Chain Analysis of SiC ...

A Manufacturing Cost and Supply Chain Analysis of SiC Power Electronics Applicable to Medium-Voltage Motor Drives Kelsey Horowitz, Timothy Remo, and Samantha Reese National Renewable Energy Laboratory Prepared under Task No AM055500 Technical ...

SILICON RF POWER MOSFET - Advanced Semiconductor

ψ VSWR = 30:1 AT ALL PHASE ANGLES NO DEGRADATION IN OUTPUT POWER SILICON RF POWER MOSFET MRF150 DESCRIPTION: The MRF150 is an N-Channel Enhancement-Mode MOS Broadband RF Power Transistor Designed for Wideband Large Signal Amplifier Applications From 20 to 150 MHz MAXIMUM RATINGS ID 16 A VDSS 125 V VGS \pm 40 V PDISS 300 W @ TC = 25 OC TJ